

10,622,863

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L9	202	tseng-horng-huei.in.	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/03/07 14:49
L10	2215	"flash memory" and (STI or "shallow trench isolation")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 14:51
L12	896	("silicon dioxide" or oxide or dielectric) same (trench or groove) same pattern\$4 same spacer same (metal or conductive or polysilicon)	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/07 14:55
L13	102	10 and 12	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/07 14:54
L14	13828	("silicon dioxide" or oxide or dielectric) and (trench or groove) and pattern\$4 and spacer and (metal or conductive or polysilicon)	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/07 14:55
L15	693	14 and 10	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/07 14:55
L16	709	("silicon dioxide" or oxide or dielectric) same (trench or groove) same pattern\$4 same spacer same (metal or conductive or polysilicon) same gate	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/07 14:55
L17	59	("silicon dioxide" or oxide or dielectric) same (trench or groove) same pattern\$4 same spacer same (metal or conductive or polysilicon) same gate same plug	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/07 14:56
L18	3703	("silicon dioxide" or oxide or dielectric) and (trench or groove) and pattern\$4 and spacer and (metal or conductive or polysilicon) and plug	US-PGPUB; USPAT; USOCR	OR	ON	2005/03/07 14:56
L19	75	("silicon dioxide" or oxide or dielectric) same (trench or groove) same pattern\$4 same spacer same (metal or conductive or polysilicon) same gate same plug	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/03/07 14:57